Silicon Carbide Schottky Diode

650 V, 6 A

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 26 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuit

ABSOLUTE MAXIMUM RATINGS

(T_C = 25°C, Unless otherwise specified)

| Symbol | Parar | Value | Unit | |
|-----------------------------------|--|---|------|---|
| V_{RRM} | Peak Repetitive Rev | 650 | V | |
| E _{AS} | Single Pulse Avalan | 26 | mJ | |
| I _F | Continuous Rectified @ T _C < 150°C | 6.0 | Α | |
| | Continuous Rectified @ T _C < 135°C | 8.0 | | |
| I _{F, Max} | Non-Repetitive Peak Forward | $T_C = 25^{\circ}C$, 10 µs | 473 | Α |
| | Surge Current | $T_C = 150^{\circ}C, 10 \ \mu s$ | 408 | |
| I _{F, SM} | Non-Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 28 | A |
| P _{tot} | Power Dissipation | T _C = 25°C | 49 | W |
| | | T _C = 150°C | 8.3 | |
| T _J , T _{STG} | Operating and Storaç Range | –55 to +175 | °C | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

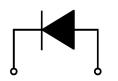
1. E_{AS} of 26 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 10.2$ A, V = 50 V.



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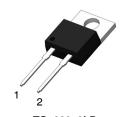
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ELECTRICAL CONNECTION



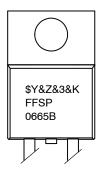
1. Cathode

2. Anode



TO-220-2LD CASE 340BB

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code &3 = Numeric Date Code

K = Lot Code

FFSP0665B = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

THERMAL CHARACTERISTICS

| Symbol | Parameter | Ratings | Unit |
|----------------|--|---------|------|
| $R_{	heta JC}$ | Thermal Resistance, Junction to Case, Max. | 2.46 | °C/W |

PACKAGE MARKING AND ORDERING INFORMATION

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|-------------|-----------|---------|----------------|-----------|------------|----------|
| FFSP0665B | FFSP0665B | TO220 | Tube | N/A | N/A | 50 Units |

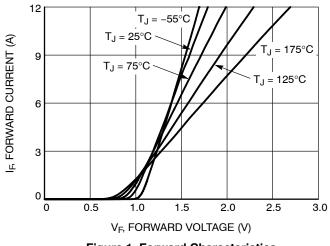
ELECTRICAL CHARACTERISTICS $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Unit |
|----------------|-------------------------|--|-----|-------|-----|------|
| V _F | Forward Voltage | I _F = 6 A, T _C = 25°C | | 1.38 | 1.7 | V |
| | | I _F = 6 A, T _C = 125°C | | 1.6 | 2.0 | |
| | | I _F = 6 A, T _C = 175°C | | 1.72 | 2.4 | |
| I _R | Reverse Current | V _R = 650 V, T _C = 25°C | | 0.025 | 40 | μΑ |
| | | V _R = 650 V, T _C = 125°C | | 0.08 | 80 | |
| | | V _R = 650 V, T _C = 175°C | | 0.22 | 160 | |
| Q _C | Total Capacitive Charge | V = 400 V | | 15 | | nC |
| С | Total Capacitance | V _R = 1 V, f = 100 kHz | | 259 | | pF |
| | | V _R = 200 V, f = 100 kHz | | 29 | | |
| | | V _R = 400 V, f = 100 kHz | | 23 | | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

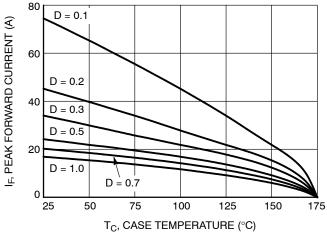
T_J = 25°C Unless Otherwise Noted



10⁻⁶ IR, REVERSE CURRENT (A) T_J = 175°C 10⁻⁷ $T_J = 125^{\circ}C$ 10⁻⁸ $T_J = 75^{\circ}C$ $T_J = 25^{\circ}C$ $T_J = -55^{\circ}C$ 10⁻⁹ 100 300 200 400 500 600 650 V_R, REVERSE VOLTAGE (V)

Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics



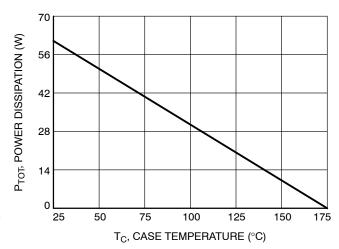
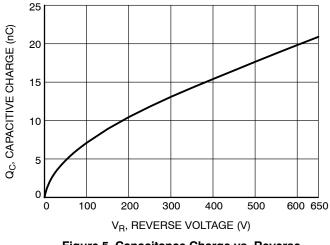


Figure 3. Current Derating

Figure 4. Power Dissipation



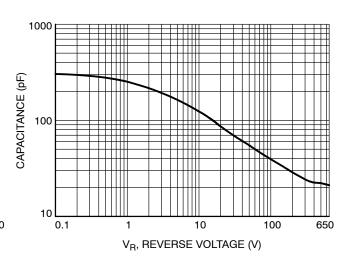


Figure 5. Capacitance Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS

 $T_J = 25^{\circ}C$ Unless Otherwise Noted (continued)

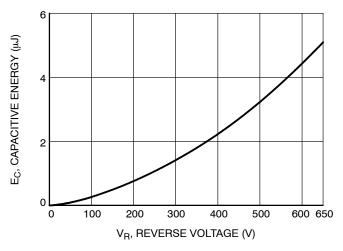


Figure 7. Capacitance Stored Energy

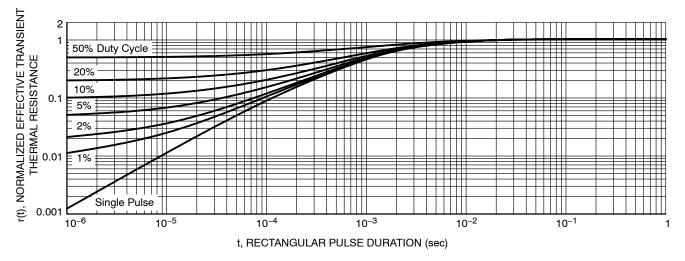


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

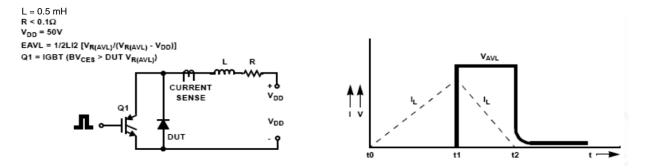
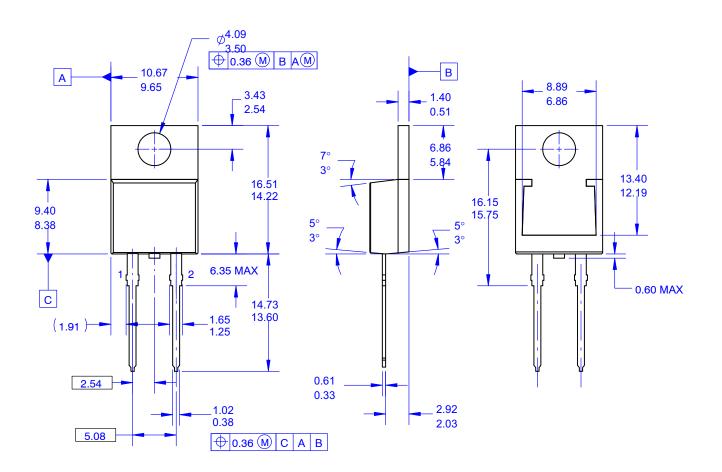


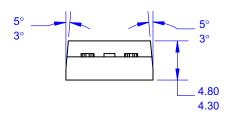
Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



TO-220-2LD CASE 340BB ISSUE O

DATE 31 AUG 2016





NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5–2009.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

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| DESCRIPTION: | TO-220-2LD | | PAGE 1 OF 1 | |

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